
2SC5470

Silicon NPN Triple Diffused
Character Display Horizontal Deflection Output

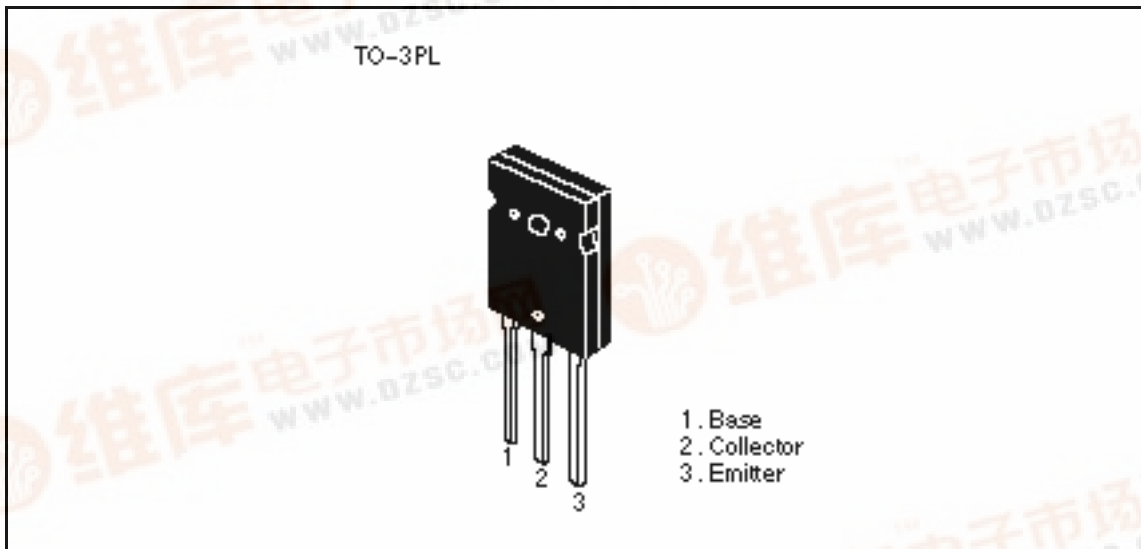
HITACHI

3rd. Edition
December 1997
Target Specification

Features

- High breakdown voltage
 $V_{CBO} = 1500\text{ V}$
- High speed switching
 $t_r = 0.15\ \mu\text{sec (typ.)}$ at $f_H = 64\text{kHz}$

Outline



2SC5470

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	1500	V
Collector to emitter voltage	V_{CEO}	700	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	20	A
Collector peak current	$i_{c(peak)}$	40	A
Collector power dissipation	P_C ^{Note1}	150	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

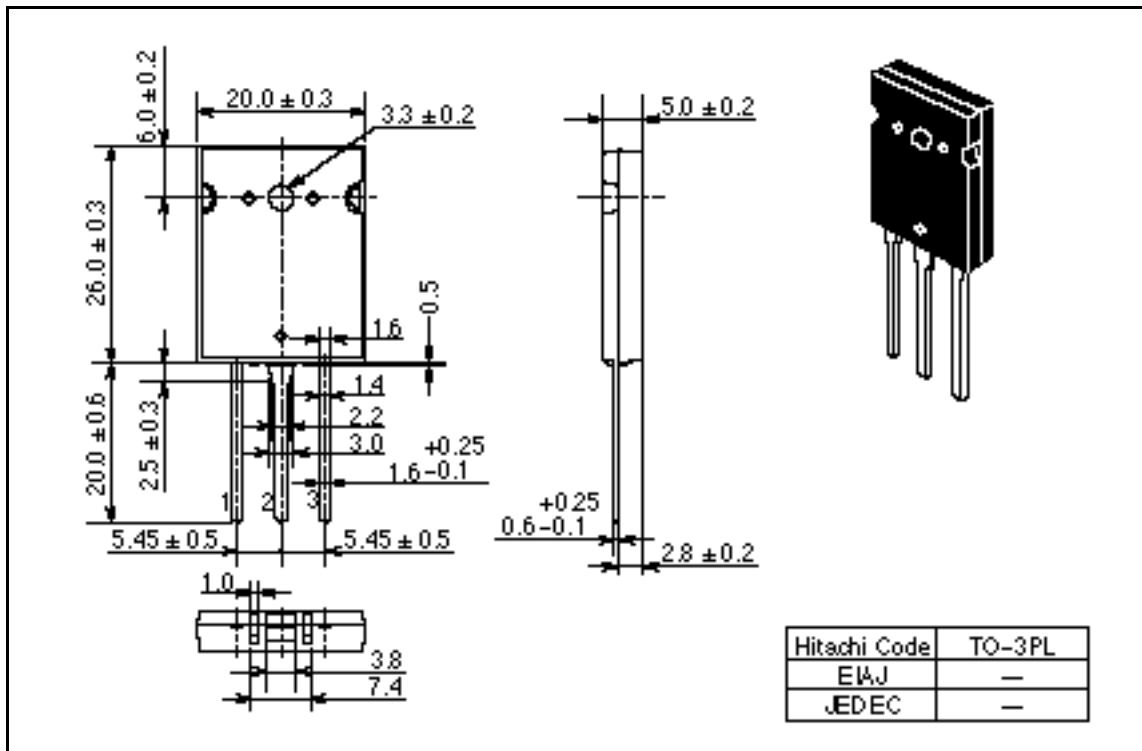
Note: 1. Value at $T_c = 25^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	700	—	—	V	$I_C = 10\text{mA}$, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10\text{mA}$, $I_C = 0$
Collector cutoff current	I_{CES}	—	—	500	μA	$V_{CE} = 1500\text{V}$, $R_{BE} = 0$
DC current transfer ratio	h_{FE1}	10	—	40		$V_{CE} = 5\text{V}$, $I_C = 1\text{A}$
DC current transfer ratio	h_{FE2}	3.5	—	6.5		$V_{CE} = 5\text{V}$, $I_C = 10\text{A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5	V	$I_C = 12\text{A}$, $I_B = 4\text{A}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 12\text{A}$, $I_B = 4\text{A}$
Fall time	t_f	—	0.2	0.4	μs	$I_{CP} = 8\text{A}$, $I_{B1} = 3\text{A}$ $f_H = 31.5\text{kHz}$
Fall time	t_f	—	0.15	—	μs	$I_{CP} = 8\text{A}$, $I_{B1} = 2\text{A}$ $f_H = 64\text{kHz}$

Package Dimensions

Unit: mm



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